

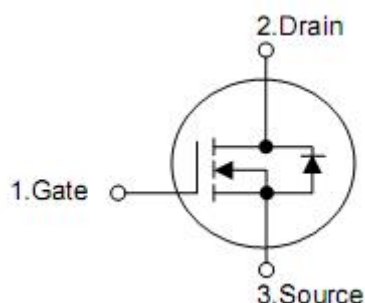
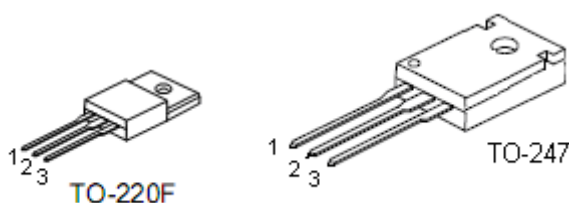
1. Description

This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

2. Features

- n Robust high voltage termination
- n Avalanche energy specified
- n Source-to-drain diode recovery time comparable to a discrete fast recovery diode
- n Diode is characterized for use in bridge circuits
- n I_{DSS} and $V_{DS(ON)}$ specified at elevated temperature
- n Isolated mounting hole reduces mounting hardware

3. Symbol



Pin	Function
1	Gate
2	Drain
3	Source

4. Absolute maximum ratings

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating		Units	
		TO-220F	TO-247		
Gate-to-source voltage continue	V_{GS}	± 20		V	
Junction and storage temperature range	T_J, T_{STG}	-55 to 150		$^{\circ}\text{C}$	
Drain to current	continuous	I_{D1}	47	A	
	pulsed	I_{DM}	141	A	
Single pulsed drain-to-source avalanche energy $T_J=25^{\circ}\text{C}^2$	E_{AS}	720		mJ	
Total power dissipation		P_D	50	417	W
			Derate above 25°C	0.4	2.78
Maximum lead temperature for soldering purposes, $1/8''$ from case for 10secods	T_L	260		$^{\circ}\text{C}$	

5. Thermal characteristics

Parameter	Symbol	Rating	Unit
Thermal resistance, Junction-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$
Thermal resistance, Junction-case	$R_{\theta JC}$	0.3	$^{\circ}\text{C}/\text{W}$

1. Drain current limited by maximum junction temperature.
2. Eas: $V_{DD}=100\text{V}$, $V_{GS}=10\text{V}$, $I_L=12\text{A}$, $L=10\text{mH}$, $R_G=25\Omega$

6. Electrical characteristics

($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_{DS}=250\mu A$	600	-	-	V
Drain-source leakage current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$	-	-	1	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V
Gate-source leakage current-forward	I_{GSSF}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Gate-source leakage current-reverse	I_{GSSR}	$V_{GS}=-20V, V_{DS}=0V$	-	-	-100	nA
Static drain-source on-resistance	$R_{DS(on)^*}$	$V_{GS}=10V, I_D=15.6A$	-	68	81	$m\Omega$
Forward on-voltage(1)	V_{SD}^*	$I_S=20A$ $d_I/d_t=100A/us$	-	-	1.5	V
Reverse recovery time	t_{rr}		-	450	-	nS
Forward turn-on time	t_{on}		-	**	-	nC
Input capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1MHz$	-	3111.9	-	pF
Output capacitance	C_{oss}		-	2399.1	-	
Reverse transfer capacitance	C_{rss}		-	61.6	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=300V, I_D=20A$ $R_G=25\Omega^*$	-	45.5	-	ns
Rise time	t_r		-	120.56	-	
Turn-off delay time	$t_{d(off)}$		-	137.06	-	
Fall time	t_f		-	116.2	-	
Total gate charge	Q_g	$V_{DS}=480V, I_D=20A$ $V_{GS}=10V^*$	-	87.967	-	nC
Gate-source charge	Q_{gs}		-	21.758	--	
Gate-drain charge	Q_{gd}		-	41.14	--	

Note *:Pulse test;pulse width $\leq 300\mu s$ duty cycle $\leq 2\%$.

** :Negligible, dominated by circuit inductance.

7. Test circuits and waveforms

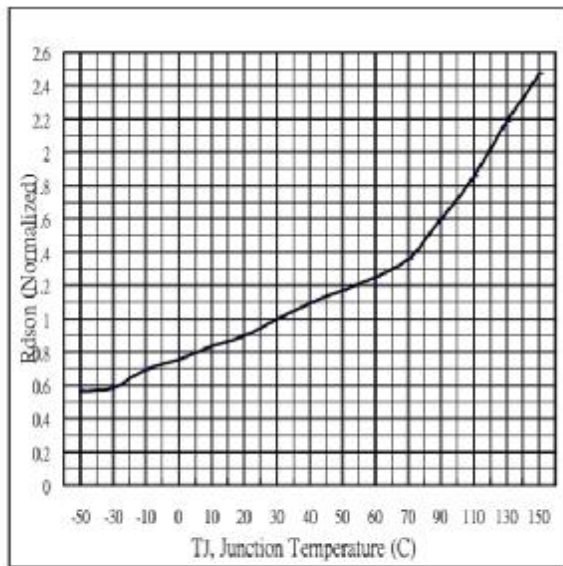


Fig 1. On-Resistance Variation with vs. Temperature

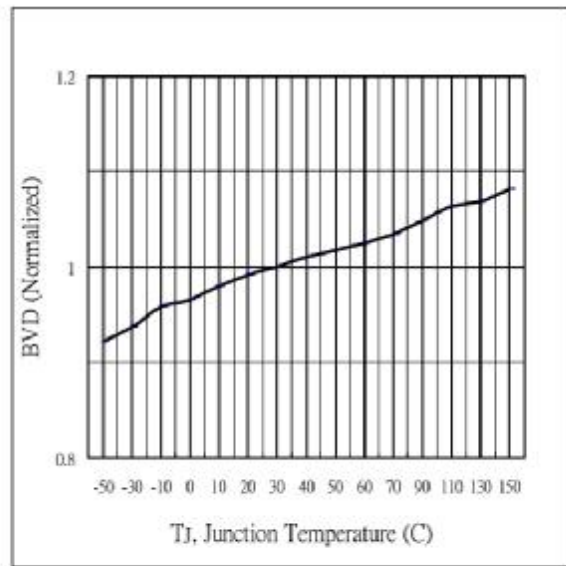


Fig.2 Breakdown Voltage Variation vs. Temperature

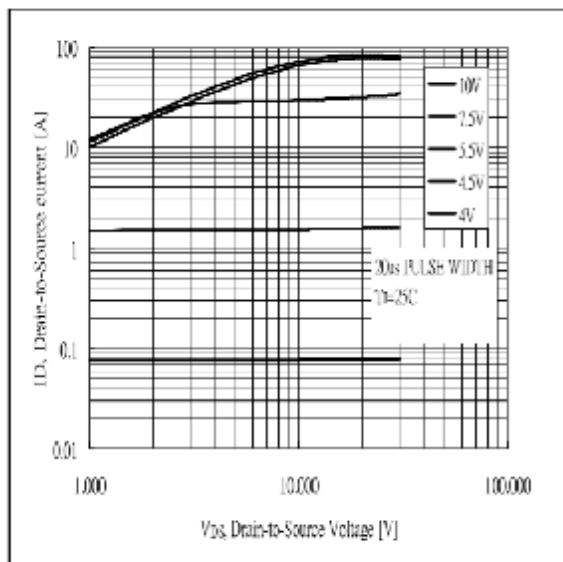


Fig 3. Typical Output Characteristics

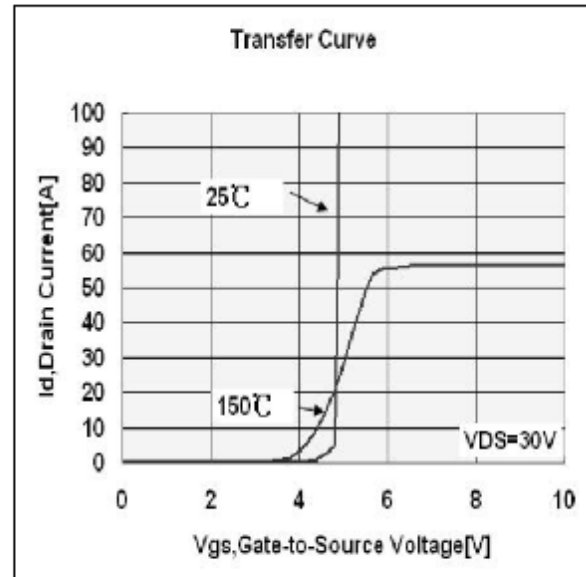


Fig 4. Typical Transfer Characteristics

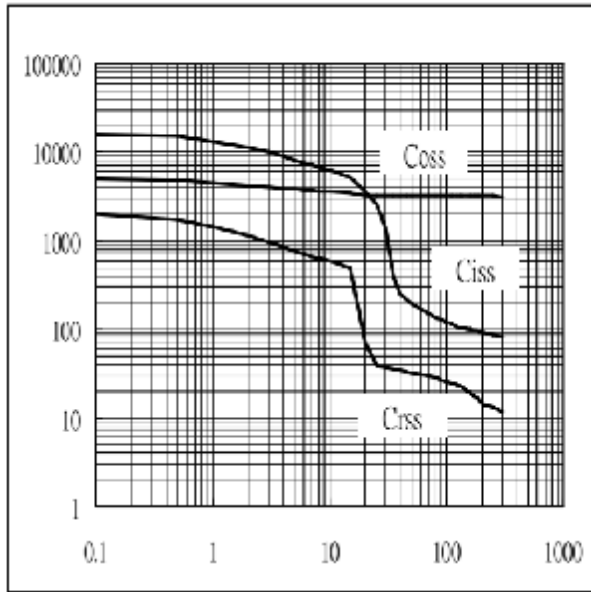


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

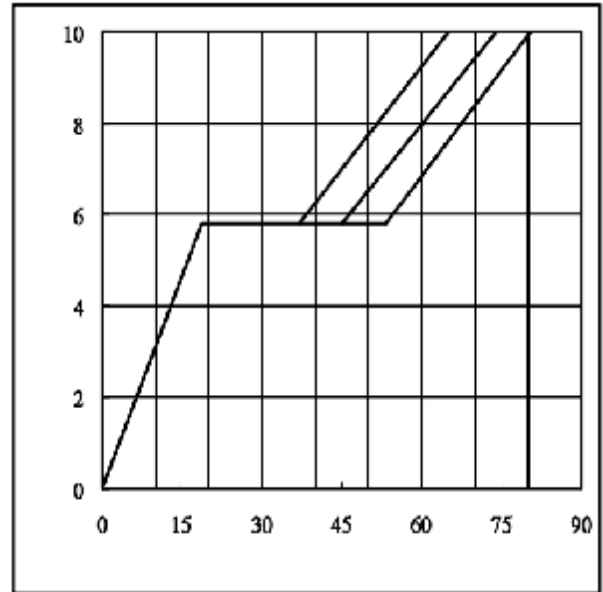


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage